

PDFN3.3X3.3-8 N Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管

■ Features 特点

Low on-resistance 低导通电阻

$R_{DS(ON)}=16m\Omega(\text{Type})@V_{GS}=10V$

$R_{DS(ON)}=21m\Omega(\text{Type})@V_{GS}=4.5V$

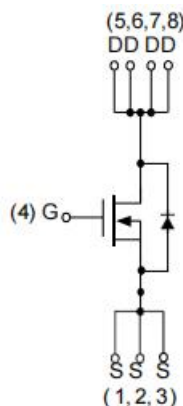
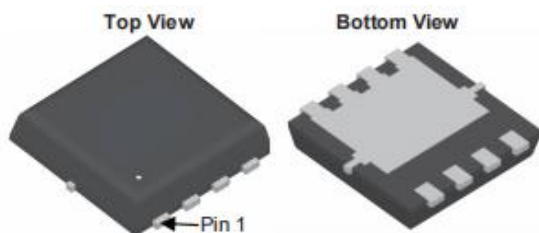
■ Applications 应用

Load Switch 负载开关

Portable Equipment 桌面设备

Power Management 电源管理

■ Internal Schematic Diagram 内部结构



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	30	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_C = 25^\circ C$ at $T_A = 25^\circ C$)	23 8	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	28	A
Total Device Dissipation 总耗散功率	P_{TOT} (at $T_C = 25^\circ C$ at $T_A = 25^\circ C$)	17.8 1.56	W
Avalanche Energy(Single Pulse)雪崩能量	E_{AS}	12	mJ
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JC}/R_{\theta JA}$	7/80	$^\circ C/W$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ Electrical Characteristics 电特性

 (T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D =250uA, V _{GS} =0V)	BV _{DSS}	30	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D =250uA, V _{GS} =V _{DS})	V _{GS(th)}	1.4	1.8	2.5	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} =24V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 栅极漏电流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =8A, V _{GS} =10V) (I _D =5A, V _{GS} =4.5V)	R _{DS(ON)}	—	16 21	21 26	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} =1A, V _{GS} =0V)	V _{SD}	—	0.75	1.1	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} =15V, f=1MHz)	C _{ISS}	—	415	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} =15V, f=1MHz)	C _{OSS}	—	70	—	pF
Reverse Transfer Capacitance 反馈电容 (V _{GS} =0V, V _{DS} =15V, f=1MHz)	C _{RSS}	—	40	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} =15V, I _D =8A, V _{GS} =4.5V)	Q _g	—	8	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} =15V, I _D =8A, V _{GS} =4.5V)	Q _{gs}	—	2	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} =15V, I _D =8A, V _{GS} =4.5V)	Q _{gd}	—	3	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} =15V I _D =1A, R _{GEN} =6Ω, V _{GS} =10V)	t _{d(on)}	—	6	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} =15V I _D =1A, R _{GEN} =6Ω, V _{GS} =10V)	t _r	—	9	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} =15V I _D =1A, R _{GEN} =6Ω, V _{GS} =10V)	t _{d(off)}	—	14	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} =15V I _D =1A, R _{GEN} =6Ω, V _{GS} =10V)	t _f	—	4	—	ns

■ Typical Characteristic Curve 典型特性曲线

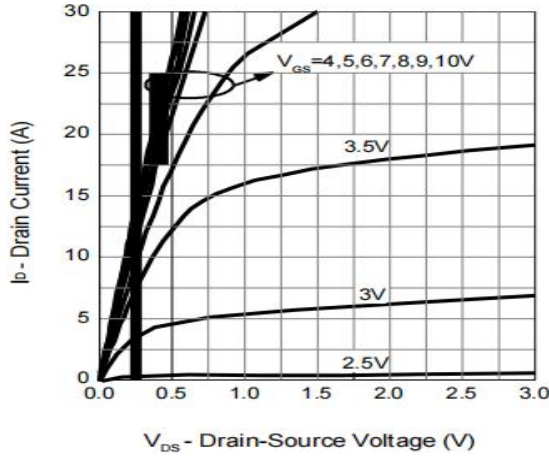


Figure 1: Output Characteristics

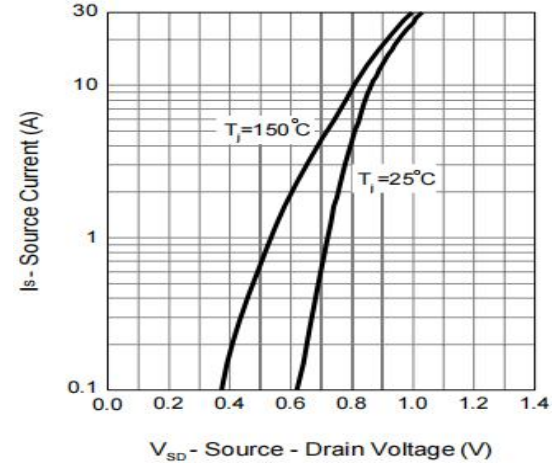


Figure 2: Diode Forward Characteristics

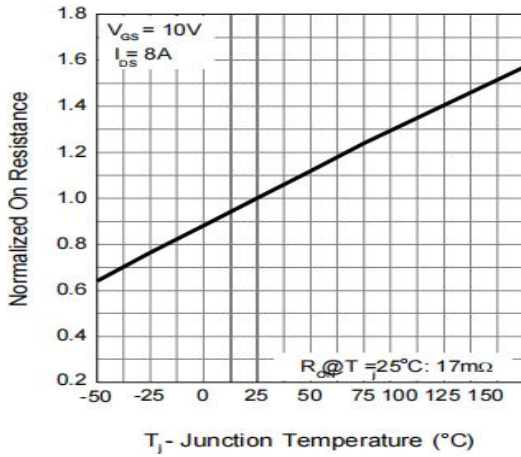


Figure 3: On-Resistance vs. T_J

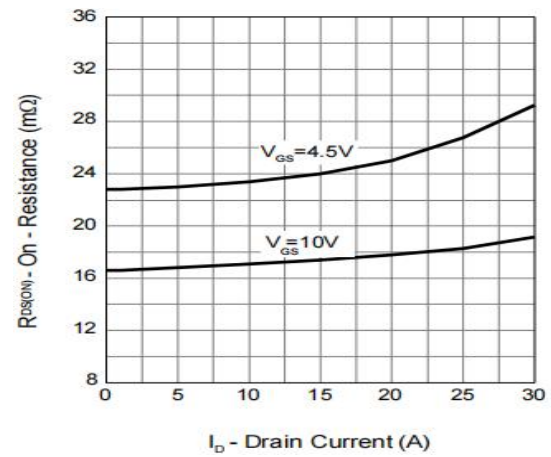


Figure 4: On-Resistance vs. Drain Current

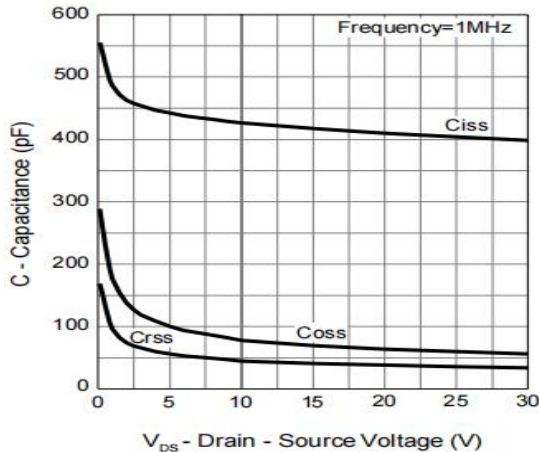


Figure 5: Capacitance Characteristics

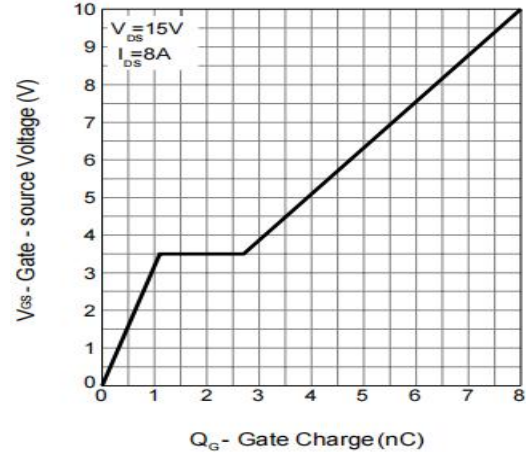
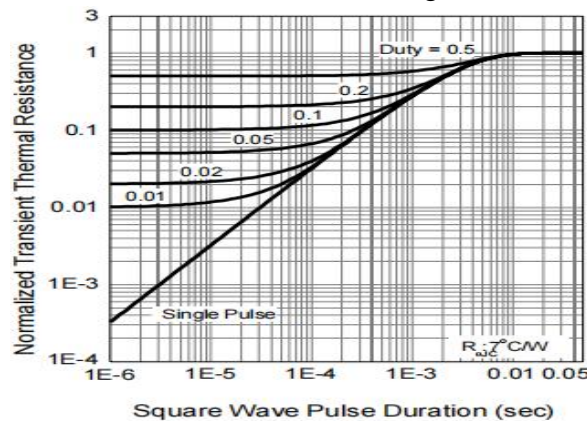
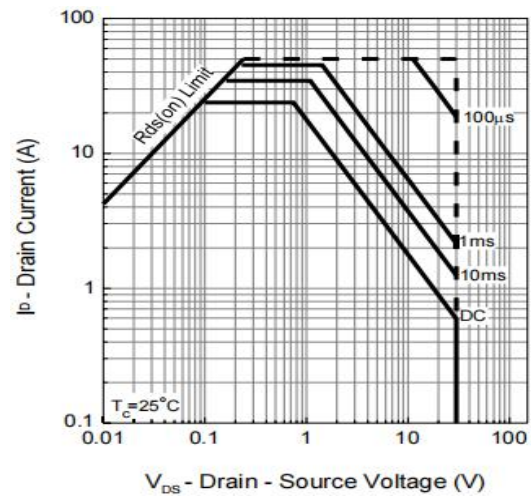
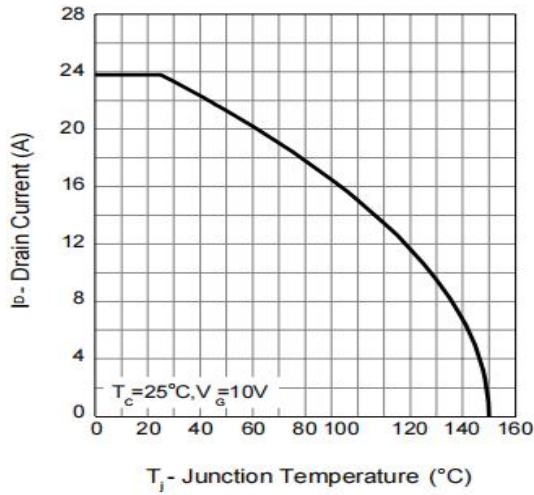
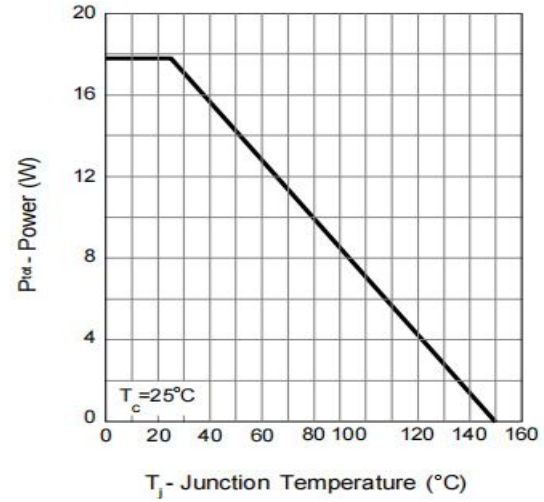
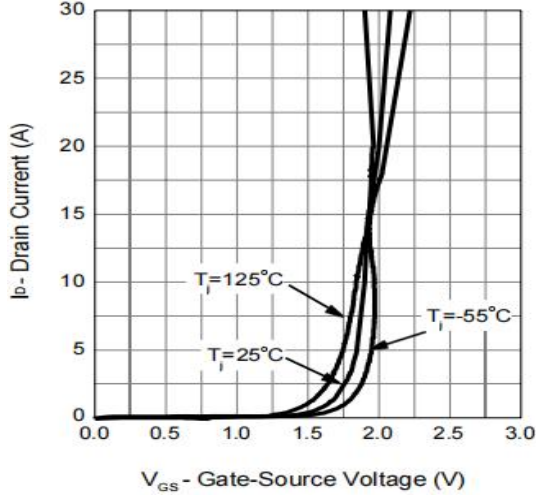
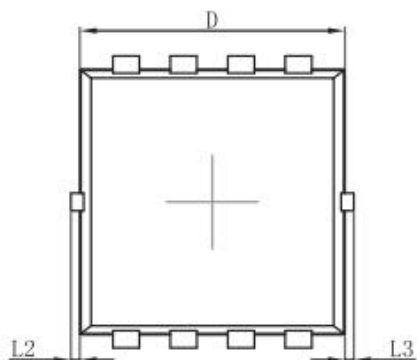


Figure 6: Gate-Charge Characteristics

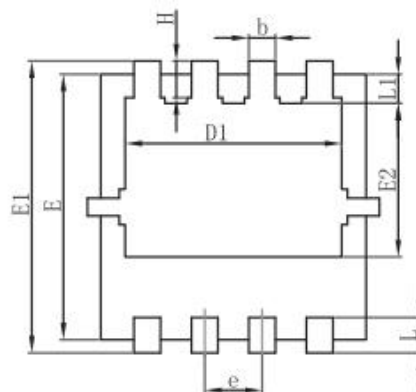
■ Typical Characteristic Curve 典型特性曲线



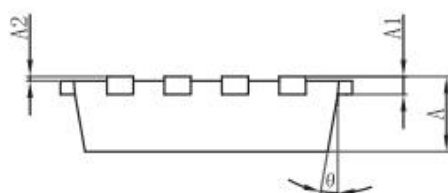
■ Dimension 外形封装尺寸



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°